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CERTIFICATE OF MAILING

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PATENT

Attorney Docket No. NTI-024 (745)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application

Inventor(s): Fang-Cheng Chang.

Application No.: 09/941,453-6364

Filed: 8/28/2001

Title **SYSTEM AND METHOD FOR IDENTIFYING
DUMMY FEATURES ON A MASK LAYER**

PATENT APPLICATION

Art Unit: unknown

Examiner: unknown

INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. §1.97

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

Listed below or on an attached Form PTO-1449 is information known to applicant(s). A copy of each listed publication and U.S. and foreign patent, except for pending U.S. applications, is being submitted herewith, along with a concise explanation of information in a foreign language, if any, pursuant to 37 C.F.R. §1.97-1.98.

Applicants respectfully request that the listed information be considered by the Examiner and be made of record in the above-identified application. If form PTO-1449 is enclosed, the Examiner is requested to initial and return it in accordance with MPEP § 609.


This statement is not intended to represent that a search has been made or that the information cited in the statement is, or is considered to be, material to patentability as defined in 37 C.F.R. § 1.56.

- ☒ This statement qualifies under *37 C.F.R. § 1.97*, subsection (b) because (check all that apply):
- ☐ (1) It is being filed within 3 months of the application filing date and is other than a continued prosecution application under § 1.53(d)
-- OR --
 - ☐ (2) It is being filed within 3 months of entry of a national stage
-- OR --
 - ☒ (3) It is being filed before the mail date of the first Office Action on the merits.
-- OR --
 - ☐ (4) It is being filed before the mailing of a first Office Action after the filing of a request for continued examination under § 1.114
- ☐ *37 C.F.R. § 1.97(c)*. If this statement is being filed after the period specified in § 1.97(b), but before the mailing date of the earlier of a final office action under § 1.113, a notice of allowance under § 1.311, or an action that otherwise closes prosecution in the application, then:
- ☐ a certification as specified in § 1.97(e) is provided below; **or**
 - ☐ a fee of \$180.00 as set forth in § 1.17(p) is authorized below, enclosed, or included with the payment of other papers filed together with this statement.
- ☐ *37 C.F.R. § 1.97(d)*. If this statement is being filed after the period specified in § 1.97(c), but on or before payment of the issue fee, then:
- A. a certification as specified in § 1.97(e) is completed below; **and**
 - B. a fee of \$180.00 as set forth in § 1.17(p) is authorized below, enclosed, or included with the payment of other papers filed together with this statement.
- ☒ *Fee Authorization*. Applicant believes no fee is due. However, should a fee be found to be owing, the Commissioner is hereby authorized to charge any fees associated with this communication to Deposit Account No. 50-0574 (Docket No. NTI-024).


Respectfully submitted,

BEVER, HOFFMAN & HARMS, LLP

Dated: March 12, 2002

By: 
Jeanette S. Harms, Reg. No. 35,537

Telephone: (408) 451-5907
Customer No. 029477

INFORMATION DISCLOSURE CITATION 	Atty. Docket No.	Serial No.
	NTI-024	09/941,453-6364
	Applicant	
	CHANG, Fang-Cheng	
	Filing Date	Group
	8/28/2001	Not Yet Assigned

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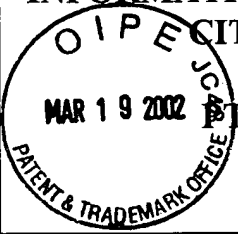
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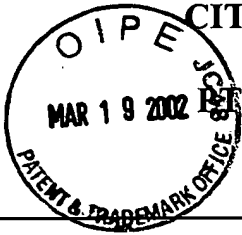
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		Applicant CHANG, Fang-Cheng		Group Not Yet Assigned			
		Filing Date 8/28/2001					
FOREIGN PATENT DOCUMENTS							
EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
	WO 00/36525 A2	6/22/2000	WO			<input type="checkbox"/>	<input type="checkbox"/>
	WO 00/67074 A1	11/9/2000	WO			<input type="checkbox"/>	<input type="checkbox"/>
	WO 00/67075 A1	11/9/2000	WO			<input type="checkbox"/>	<input type="checkbox"/>
	WO 00/67076 A1	11/9/2000	WO			<input type="checkbox"/>	<input type="checkbox"/>

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**INFORMATION DISCLOSURE
CITATION**

PTO-1449

Atty. Docket No.

NTI-024

Serial No.

09/941,453-636

Applicant

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